

HCBC556/HCBC557/HCBC558(PNP)

GENERAL PURPOSE TRANSISTOR

REPLACEMENT TYPE: BC556/BC557/BC558

FEATURES

- Low current
- High Voltage
- Complement to HCBC546,HCBC547,HCBC548



TO-92

1: COLLECTOR 2: BASE 3: EMITTER

MAXIMUM RATINGS ($T_A = 25^{\circ}$ C unless otherwise noted)

Parameter	Symbol	Value	Unit	
	BC546		-80	V
Collector-Base Voltage	BC547	V _{CBO}	-50	
	BC548		-30	
	BC546		-65	
Collector-Emitter Voltage	BC547	V _{CEO}	-45	V
	BC548		-30	
Emitter-Base Voltage	BC546		-5	V
	BC547	V _{EBO}	-5	V
	BC548		-5	V
Collector Current-Continuous	Ic	-0.1	Α	
Collector Power Dissipation	Pc	625	mW	
Thermal Resistance from Junction to Amb	R _{θJA}	200	°C/W	
Junction Temperature	T _j	150	$^{\circ}$	
Storage Temperature	T _{stg}	-55~+150	$^{\circ}$	



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ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Parameter		Symbol	Test conditions	Min	Тур	Max	Unit
	BC556			-80			V
Collector-Base Breakdown Voltage	BC557	V _{CBO}	I _C = -0.1mA , I _E =0	-50			
	BC558			-30			
	BC556			-65			V
Collector-Emitter Breakdown Voltage	BC557	V _{CEO}	I _C =-2mA, I _B =0	-45			
	BC558			-30			
	BC556			-5			. v
Emitter-Base Breakdown Voltage	BC557	V _{EBO}	I _E =-100μA, I _C =0	-5			
	BC558			-5			
Collector Cut-off Current	BC556		V _{CB} =-70V, I _E =0			-0.1	μA
	BC557	I _{CBO}	V _{CB} =-45V, I _E =0			-0.1	μA
	BC558		V _{CB} =-25V, I _E =0			-0.1	μA
	BC556		V _{CE} =-60V, I _B =0			-0.1	μA
Collector Cut-off Current	BC557	I _{CEO}	V _{CE} =-45V, I _B =0			-0.1	μA
	BC558		V _{CE} =-20V, I _B =0			-0.1	μA
Emitter Cut-off Current		I _{EBO}	V _{EB} =-5V, I _C =0			0.1	μA
DC Current Gain		h _{FE}	V _{CE} =-5V, I _C =-2mA	120		800	
Collector-Emitter Saturation Voltage		V _{CE(sat)}	I _C =-10mA, I _B =-0.5mA			0.3	V
			I _C =-100mA, I _B =-5mA			0.65	V
Base-Emitter Saturation Voltage		V _{BE(sat)}	I _C =-10mA, I _B =-0.5mA			0.8	V
			I _C =-100mA, I _B =-5mA			1	V
Base-Emitter Voltage		V	V _{CE} =-5V, I _C =-2mA	-0.55		-0.7	V
		V _{BE}	V _{CE} =-5V, I _C =-10mA			-0.8	V
Collector Output Capacitance		C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz			5	pF
Transition Frequency		f⊤	V _{CE} =-5V, I _C =-10mA, f=100MHz		150		MHz

CLASSIFICATION OF hFE

Rank	556A	557B	558C	
Range	110-220	200-450	420-800	

-1.0

GENERAL PURPOSE TRANSISTOR

Typical Characteristics

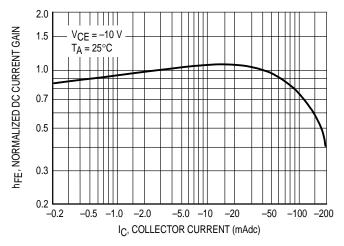


Figure 1. Normalized DC Current Gain

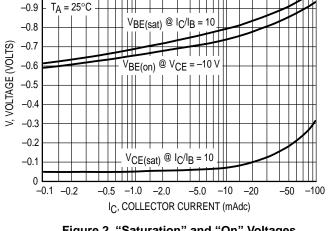


Figure 2. "Saturation" and "On" Voltages

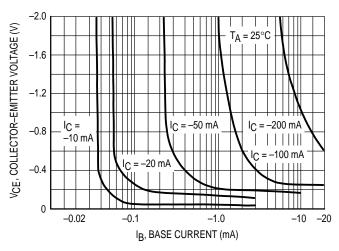


Figure 3. Collector Saturation Region

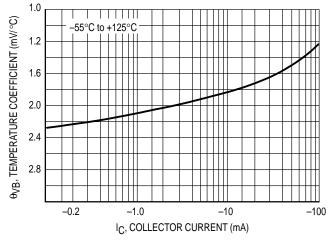


Figure 4. Base-Emitter Temperature Coefficient

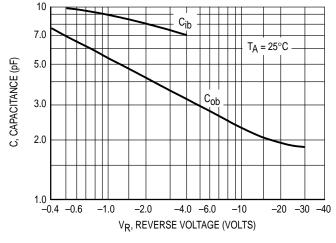


Figure 5. Capacitances

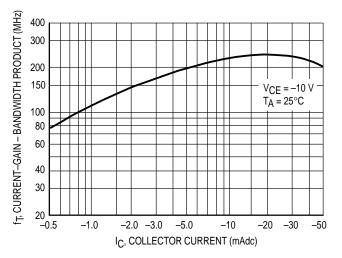


Figure 6. Current-Gain - Bandwidth Product

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GENERAL PURPOSE TRANSISTOR

BC556/BC557/BC558 Typical Characteristics

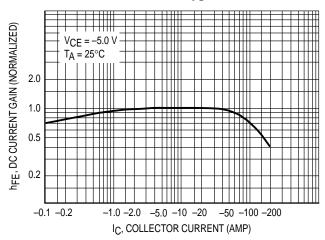


Figure 7. DC Current Gain

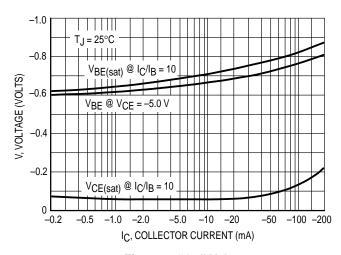


Figure 8. "On" Voltage

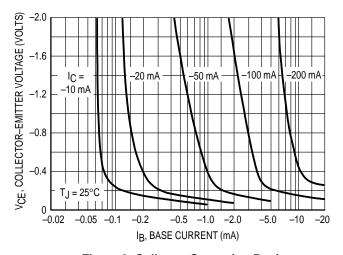


Figure 9. Collector Saturation Region

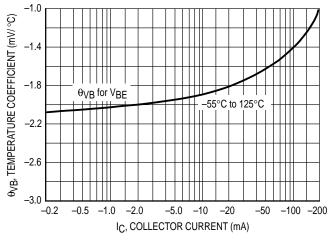


Figure 10. Base-Emitter Temperature Coefficient

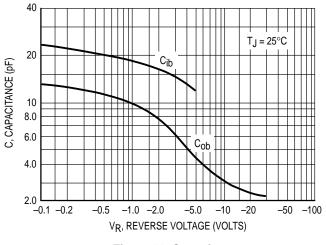


Figure 11. Capacitance

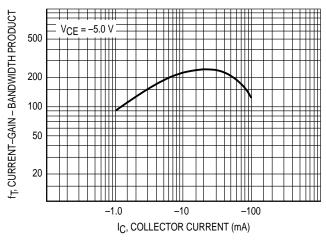
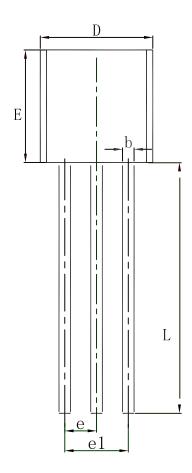


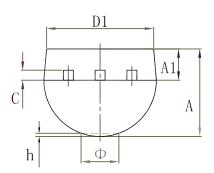
Figure 12. Current-Gain - Bandwidth Product



GENERAL PURPOSE TRANSISTOR

TO-92 Package Outline Dimensions



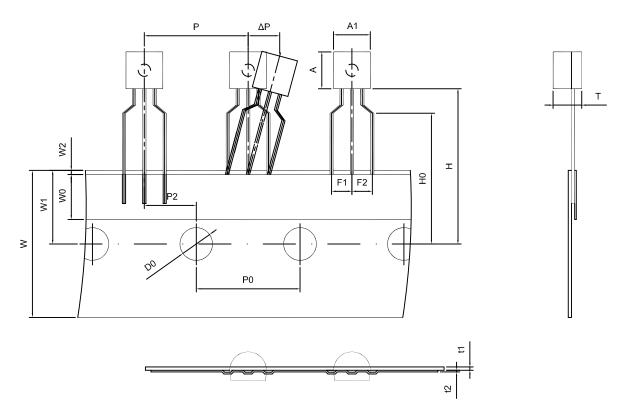


Symbol	Dimensions In N	Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	3.300	3.700	0.130	0.146	
A1	1.100	1.400	0.043	0.055	
b	0.380	0.550	0.015	0.022	
С	0.360	0.510	0.014	0.020	
D	4.300	4.700	0.169	0.185	
D1	3.430		0.135		
E	4.300	4.700	0.169	0.185	
е	1.270 TYP.		0.050 TYP.		
e1	2.440	2.640	0.096	0.104	
L	14.100	14.500	0.555	0.571	
Ф		1.600		0.063	
h	0.000	0.380	0.000	0.015	



GENERAL PURPOSE TRANSISTOR

TO-92 Package Outline Dimensions



Dimiensions are in millimeter								
A1	А	Т	Р	P0	P2	F1	F2	W
4.5±0.2	4.5±0.2	3.5±0.2	12.7±0.3	12.7±0.2	6.35±0.3	2.5±0.3	2.5±0.3	18.0+1.0/-0.5
WO	W1	W2	Н	H0	D0	t1	t2	ΔΡ
6.0±0.5	9.0±0.5	1.0 MAX.	19.0±1.0	16.0±0.5	4.0±0.5	0.4±0.05	0.2±0.05	0 ± 1.0

